

BC184L

SILICON NPN SMALL SIGNAL TRANSISTOR

$V_{CE0} \dots 30 \text{ V (Min)}$

$h_{FE} \dots 130 \text{ (Min) @ } V_{CE} = 5.0 \text{ V, } I_C = 100 \text{ mA}$

ABSOLUTE MAXIMUM RATINGS (NOTE 1)

TEMPERATURES

Storage Temperature $-55 \text{ Degrees C to } 150 \text{ Degrees C}$

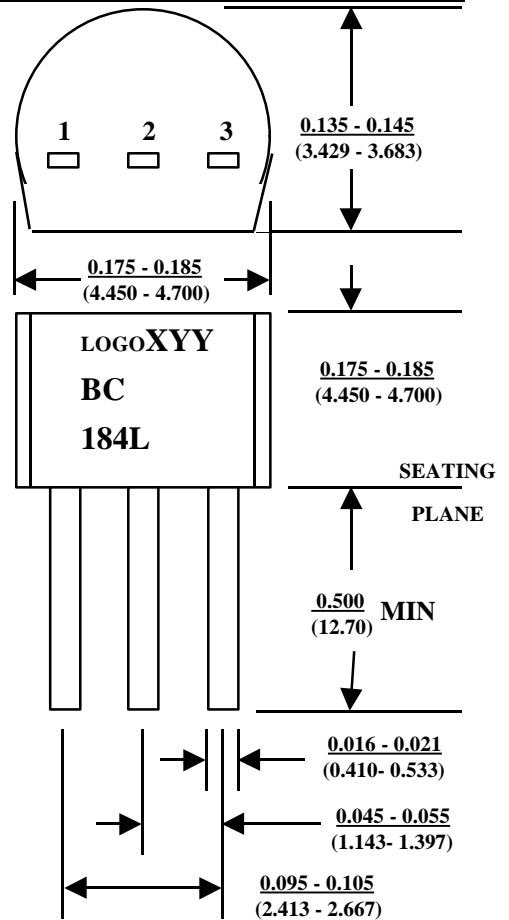
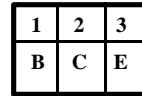
Operating Junction Temperature 150 Degrees C

POWER DISSIPATION (NOTES 2 & 3)

Total Device Dissipation at $T_A = 25$

VOLTAGES & CURRENT

V_{CE0}	Collector to Emitter	30 V
V_{CBO}	Collector to Base	45 V
V_{EBO}	Emitter to Base	5 V
I_C	Collector Current	500 mA



ELECTRICAL CHARACTERISTICS (25 Degrees C Ambient Temperature unless otherwise stated)

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
V_{CBO}	Collector to Base Voltage	45		V	$I_C = 10 \text{ uA}$
V_{CE0}	Collector to Emitter Voltage	30		V	$I_C = 2.0 \text{ mA}$
V_{EBO}	Emitter to Base Voltage	5		V	$I_E = 10 \text{ uA}$
I_{CBO}	Collector Cutoff Current		15	nA	$V_{CB} = 30 \text{ V}$
I_{EBO}	Emitter Cutoff Current		15	nA	$V_{EB} = 4 \text{ V}$
h_{FE}	DC Current Gain	100 130			$V_{CE} = 5.0 \text{ V } I_C = 10 \text{ uA}$ $V_{CE} = 5.0 \text{ V } I_C = 100 \text{ mA}$
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		0.6	V	$I_C = 10 \text{ mA } I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA } I_B = 5.0 \text{ mA}$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage				$I_C = 100 \text{ mA } I_B = 5.0 \text{ mA}$
$V_{BE(on)}$	Base -Emitter On Voltage	0.55	0.7	V	$V_{CE} = 5.0 \text{ V } I_C = 2 \text{ mA}$

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ELECTRICAL CHARACTERISTICS Con't (25 Degrees C Ambient Temperature unless otherwise stated)

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
COB	Output Capacitance		5.0	pF	V _{CB} = 10 V, f = 1 MHz
f _T	Current Gain - Bandwidth Product				V _{CE} = 5 V I _C = 10 mA f = 100 Mhz
h _{fe}	Small Signal Current Gain	240	900	-	V _{CE} = 5 V, I _C =2.0 mA, f=1KHz
NF	Noise Figure		4	dB	V _{CE} = 5 V, I _C = 200 uA, R _g = 2 Kohms, f = 30Hz-15kHz

NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 These ratings are based on a maximum junction temperature of 150 degrees C.

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